

WSK330N04G6

N-Channel MOSFET

General Description

The WSK330N04G6 advanced SGT technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with gate voltages as low as 4.5V.

This device is suitable for use as a Battery protection or in other Switching application.

Features

- Advanced high cell density Trench technology
- Super Low Gate Charge
- Excellent CdV/dt effect decline
- 100% E_{AS} Guaranteed
- Green Device Available

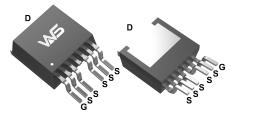
Product Summery

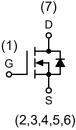
BV _{DSS}	R _{DS(ON)}	Ι _D
40V	1.0mΩ	330A

Applications

- Battery protection
- Load switch.
- Uninterruptible power supply

TO-263-6L Pin Configuration





Absolute Maximum Ratings

Symbol	nbol Parameter Rating		Units
V _{DS}	Drain-Source Voltage	40	V
V _{GS}	Gate-Source Voltage	±20	V
I _D @T _C =25°C	Continuous Drain Current, V _{GS} @ 10V	330	
I _D @T _C =100°C	Continuous Drain Current, V _{GS} @ 10V	212	А
I _{DM}	Pulsed Drain Current ²	528	
E _{AS}	Single Pulse Avalanche Energy ³	1125	mJ
I _{AS}	Avalanche Current	150	А
P _D @T _C =25°C	Total Power Dissipation ⁴	125	W
T _{STG}	Storage Temperature Range	-55 to 150	°C
TJ	Operating Junction Temperature Range	-55 to 150	U U

Thermal Data

Symbol	Parameter	Rating	Units
R _{θJA}	Thermal Resistance Junction-Ambient ¹	50	°C/W
R _{θJC}	Thermal Resistance Junction-Case ¹	1.0	C/W



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Electrical Characteristics (T_J=25°C, Unless Otherwise Noted)

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Units	
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V , I _D =250µA	40			V	
$\Delta BV_{DSS}/\Delta T_{J}$	BV _{DSS} Temperature Coefficient	Reference to 25°C, I _D =1mA		0.043		V/°C	
D	Static Drain-Source On-Resistance ²	V _{GS} =10V , I _D =25A		1.0	1.5	— mΩ	
R _{DS(ON)}		V _{GS} =4.5V , I _D =15A		1.5	2.1		
V _{GS(th)}	Gate Threshold Voltage		1.0	1.8	2.5	V	
$\Delta V_{GS(th)}$	V _{GS(th)} Temperature Coefficient	- V _{GS} =V _{DS} , Ι _D =250μΑ		-6.94		mV/°C	
1	Drain Source Lookage Current	V _{DS} =32V , V _{GS} =0V , T _J =25°C			2.0		
I _{DSS}	Drain-Source Leakage Current	V_{DS} =32V , V_{GS} =0V , T_{J} =55°C			10	μA	
I _{GSS}	Gate-Body Leakage Current	V_{GS} =±20V , V_{DS} =0V			±100	nA	
9 _{fs}	Forward Transconductance	vard Transconductance V _{DS} =10V , I _D =15A		47		S	
Qg	Total Gate Charge	V_{DS} =20V , V_{GS} =10V , I_{D} =20A		50		nC	
Qg	Total Gate Charge			23			
Q _{gs}	ate-Source Charge V_{DS} =20V , V_{GS} =4.5V , I _D =20A			9.6		nC	
Q _{gd}	Gate-Drain Charge			8.7			
T _{d(on)}	Turn-on Delay Time			18			
T _r	Rise Time	V_{DD} =20V , V_{GS} =10V , R_L =20 Ω ,		10			
T _{d(off)}	Turn-off Delay Time	R _G =16Ω , I _D =1Α		57		ns	
T _f	Fall Time			51			
C _{iss}	Input Capacitance			9500			
C _{oss}	Output Capacitance	V _{DS} =20V , V _{GS} =0V , <i>f</i> =1.0MHz		4500		pF	
C _{rss}	Reverse Transfer Capacitance			3200			

Diode Characteristics

Symbol	Parameter Conditions		Min.	Тур.	Max.	Units
ا _S	Continuous Source Current ^{1,5}	V _G =V _D =0V , Force Current			200	A
V _{SD}	Diode Forward Voltage ²	V_{GS} =0V , I_{S} =25A , T_{J} =25°C			1.3	V

Note:

1. The data tested by surface mounted on a 1 inch² FR-4 board with 2OZ copper.

2. The data tested by pulsed, pulse width $\leq 300 \mu s$, duty cycle $\leq 2\%$.

3. The $\,E_{AS}\,$ data shows Max. rating. The test condition is $\,V_{DD}$ =20V, V_{GS} =10V, L=0.1mH, I_{AS} =150A

4. The power dissipation is limited by 150°C junction temperature.

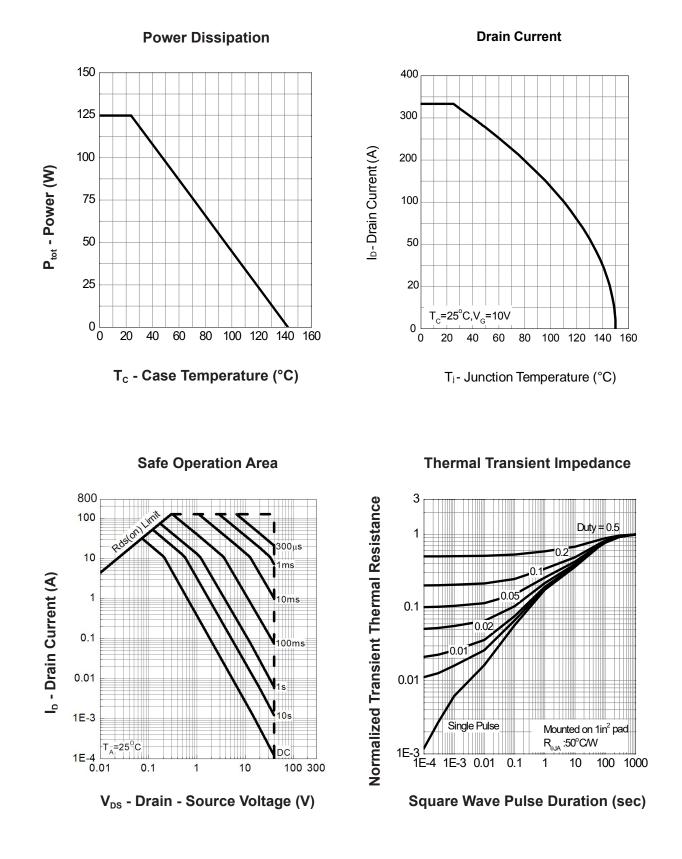
5. The data is theoretically the same as I_D and I_{DM} , in real applications, should be limited by total power dissipation.





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Typical Characteristics

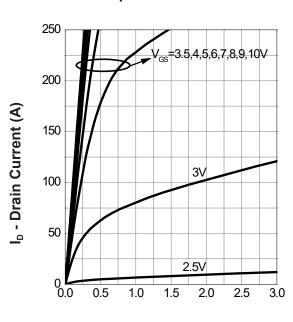






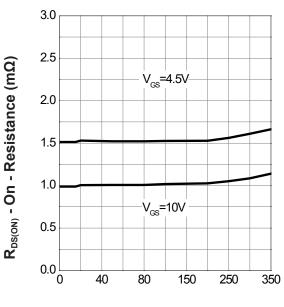
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Typical Characteristics (Cont.)

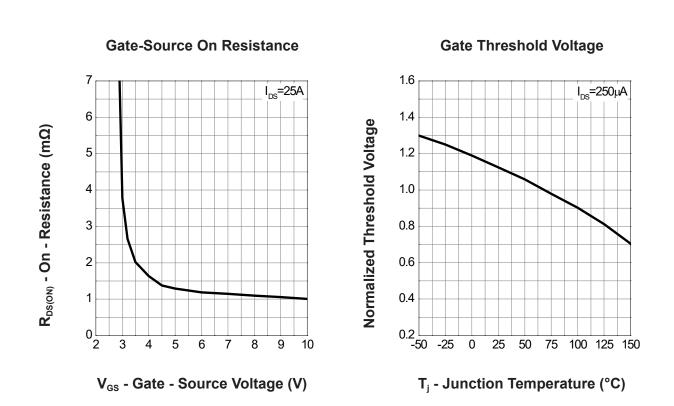


Output Characteristics

V_{DS} - Drain - Source Voltage (V)



I_D - Drain Current (A)



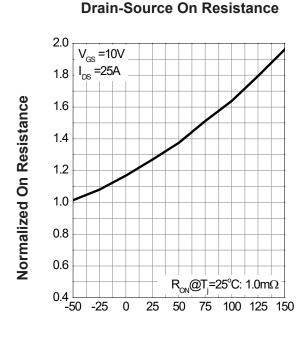
Drain-Source On Resistance





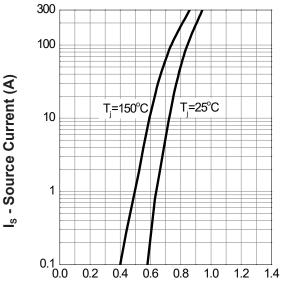
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Typical Characteristics (Cont.)

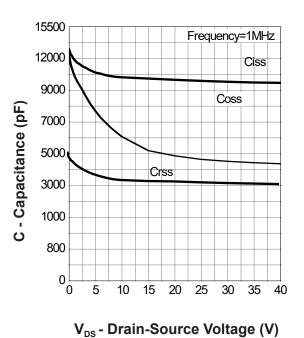


T_j - Junction Temperature (°C)

Source-Drain Diode Forward

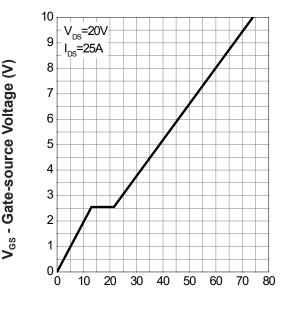


V_{SD} - Source - Drain Voltage (V)



Capacitance

Gate Charge



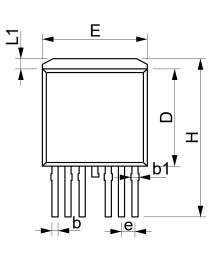


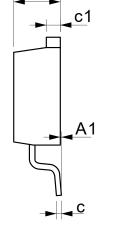


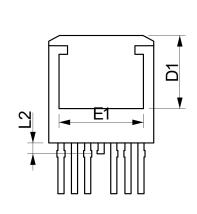
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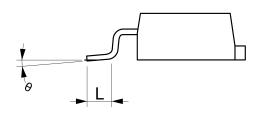
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Packaging information









SYMDOL	MILLIMETERS		INCHES		
SYMBOL	MIN.	MAX.	MIN.	MAX.	
A	4.25	4.55	0.167	0.179	
A1	0.01	0.25	0.000	0.010	
b	0.50	0.70	0.020	0.028	
b1	0.60	0.84	0.024	0.033	
С	0.40	0.60	0.016	0.024	
c1	1.20	1.40	0.047	0.055	
D	9.05	9.45	0.356	0.372	
D1	6.90	9.00	0.272	0.354	
E	9.80	10.20	0.386	0.402	
E1	7.25	9.00	0.285	0.354	
е	1.27 BSC		0.05 BSC		
Н	14.65	15.35	0.577	0.604	
L	2.40	3.00	0.094	0.118	
L1	0.80	1.20	0.031	0.047	
L2	0.85	1.15	0.330	0.045	
θ	2°	8°	2°	8°	



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